# **BAWH56W, NSVBAWH56W**

# **Dual Switching Diode, Common Anode**

#### **Features**

- 175°C T<sub>J(MAX)</sub> Rated for High Temperature, Mission Critical Applications
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

# **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Reverse Voltage	V <sub>R</sub>	70	V
Forward Current	lF	200	mA
Non-Repetitive Peak Surge Current (surge applied at rated load conditions, half wave, single pulse, 60 Hz)	I <sub>FSM</sub>	2.0	А

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

# THERMAL CHARACTERISTICS (T<sub>A</sub> = 25°C)

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1)  T <sub>A</sub> = 25°C	P <sub>D</sub>	200	mW
Derate above 25°C		1.1	mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{ heta JA}$	615	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C	P <sub>D</sub>	300	mW
Derate above 25°C		1.6	mW/°C
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature	T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C

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- 1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.
- 2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

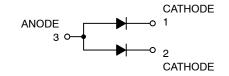


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SC-70 CASE 419 STYLE 4



#### **MARKING DIAGRAM**



CH = Device Code

M = Date Code\*

Pb-Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
BAWH56WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel
NSVBAWH56WT1G	SC-70 (Pb-Free)	3,000 / Tape & Reel

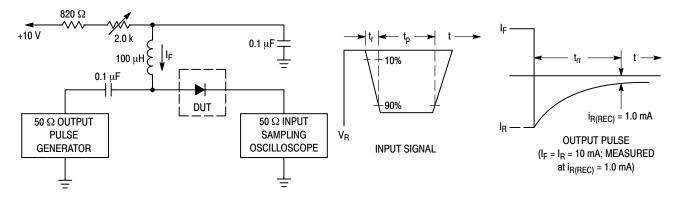
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# **BAWH56W, NSVBAWH56W**

# **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	·			
Reverse Breakdown Voltage $(I_{(BR)} = 100 \mu A)$	V <sub>(BR)</sub>	70	-	V
Reverse Voltage Leakage Current $(V_R = 25 \text{ V}, T_J = 175^{\circ}\text{C})$ $(V_R = 70 \text{ V})$ $(V_R = 70 \text{ V}, T_J = 175^{\circ}\text{C})$	I <sub>R</sub>	- - -	30 2.5 50	μΑ
Diode Capacitance (V <sub>R</sub> = 0, f = 1.0 MHz)	C <sub>D</sub>	-	2.0	pF
Forward Voltage (I <sub>F</sub> = 1.0 mA) (I <sub>F</sub> = 10 mA) (I <sub>F</sub> = 50 mA) (I <sub>F</sub> = 150 mA)	V <sub>F</sub>	- - - -	715 855 1000 1250	mV
Reverse Recovery Time (I <sub>F</sub> = I <sub>R</sub> = 10 mA, R <sub>L</sub> = 100 $\Omega$ , I <sub>R(REC)</sub> = 1.0 mA) (Figure 1)	t <sub>rr</sub>	-	6.0	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.



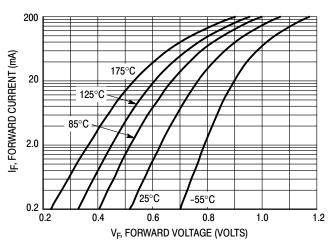
Notes: 1. A 2.0  $k\Omega$  variable resistor adjusted for a Forward Current (IF) of 10 mA.

- 2. Input pulse is adjusted so  $I_{R(peak)}$  is equal to 10 mA.
- 3.  $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

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# **TYPICAL CHARACTERISTICS**



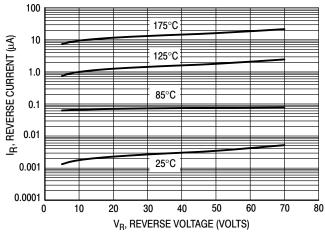


Figure 2. Forward Voltage

Figure 3. Leakage Current

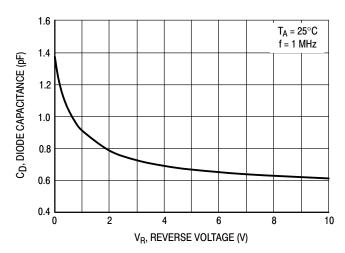


Figure 4. Capacitance





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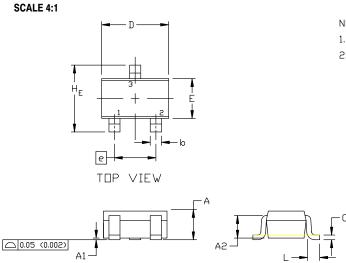
END VIEW

**DATE 11 OCT 2022** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.	
Α	0.80	0.90	1.00	0.032	0.035	0.040	
A1	0.00	0.05	0.10	0.000	0.002	0.004	
A2		0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016	
С	0.10	0.18	0.25	0.004	0.007	0.010	
D	1.80	2.00	2.20	0.071	0.080	0.087	
E	1.15	1.24	1.35	0.045	0.049	0.053	
е	1.20	1.30	1.40	0.047	0.051	0.055	
e1	0.65 BSC				0.026 BS	C	
L	0.20	0.38	0.56	0.008	0.015	0.022	
HE	2.00	2.10	2.40	0.079	0.083	0.095	



### **GENERIC MARKING DIAGRAM**

SIDE VIEW

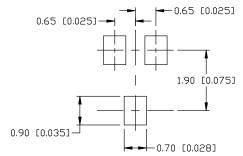


= Specific Device Code XX

М = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6: PIN 1. EMITTER	STYLE 7: PIN 1. BASE	STYLE 8: PIN 1. GATE	STYLE 9: PIN 1. ANODE	STYLE 10: PIN 1. CATHODE	STYLE 11: PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	2. CATHODE
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

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